

**DUAL N-CHANNEL ENHANCEMENT MODE MOSFET**
**Product Summary**

$V_{(BR)DSS}$	$R_{DS(ON)}$	Package	$I_D$ $T_A = +25^\circ\text{C}$
60V	8Ω @ $V_{GS} = 5V$	SOT363	170mA
	6Ω @ $V_{GS} = 10V$		200mA

**Description**

This new generation MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

**Applications**

- DC-DC Converters
- Power Management Functions
- Battery Operated Systems and Solid-State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.

**Features**

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- ESD Protected Gate, 1kV (HBM)
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

**Mechanical Data**

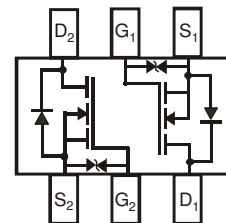
- Case: SOT363
- Case Material: Molded Plastic; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Solderable per MIL-STD-202, Method 208 (e3)
- Lead-Free Plating (Matte Tin Finish Annealed over Alloy 42 Leadframe).
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)



SOT363



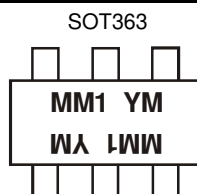
Top View


 Top View  
Internal Schematic

**Ordering Information** (Note 5)

Part Number	Case	Packaging
DMN65D8LDWQ-7	SOT363	3,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to [http://www.diodes.com/quality/product\\_grade\\_definitions/](http://www.diodes.com/quality/product_grade_definitions/).
  5. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

**Marking Information**


MM1= Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: A = 2013)  
 M = Month (ex: 9 = September)

## Date Code Key

Year	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017	2018
Code	U	V	W	X	Y	Z	A	B	C	D	E	F
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic				Symbol	Value	Units
Drain-Source Voltage				$V_{DSS}$	60	V
Gate-Source Voltage				$V_{GSS}$	$\pm 20$	V
Continuous Drain Current (Note 6)	$V_{GS} = 10\text{V}$	Steady State	$T_A = +25^\circ\text{C}$	$I_D$	180	mA
			$T_A = +70^\circ\text{C}$		140	
Continuous Drain Current (Note 6)	$V_{GS} = 5\text{V}$	Steady State	$T_A = +25^\circ\text{C}$	$I_D$	150	mA
			$T_A = +70^\circ\text{C}$		120	
Continuous Drain Current (Note 7)	$V_{GS} = 10\text{V}$	Steady State	$T_A = +25^\circ\text{C}$	$I_D$	200	mA
			$T_A = +70^\circ\text{C}$		160	
Continuous Drain Current (Note 7)	$V_{GS} = 5\text{V}$	Steady State	$T_A = +25^\circ\text{C}$	$I_D$	170	mA
			$T_A = +70^\circ\text{C}$		140	
Pulsed Drain Current (10 $\mu\text{s}$ pulse, duty cycle = 1%)				$I_{DM}$	800	mA

**Thermal Characteristics**

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 6)	$P_D$	300	mW
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	435	$^\circ\text{C/W}$
Total Power Dissipation (Note 7)	$P_D$	400	mW
Thermal Resistance, Junction to Ambient (Note 7)	$R_{\theta JA}$	330	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case (Note 7)	$R_{\theta JC}$	139	$^\circ\text{C/W}$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

**Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	60	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	1.0	$\mu\text{A}$	$V_{DS} = 60\text{V}, V_{GS} = 0\text{V}$
				5.0		
Gate-Body Leakage	$I_{GSS}$	—	—	$\pm 5.0$	$\mu\text{A}$	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	1.0	—	2.0	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	—	8	$\Omega$	$V_{GS} = 5.0\text{V}, I_D = 0.115\text{A}$
		—	—	6	$\Omega$	$V_{GS} = 10.0\text{V}, I_D = 0.115\text{A}$
Forward Transconductance	$g_{FS}$	80	—	—	mS	$V_{DS} = 10\text{V}, I_D = 0.115\text{A}$
Diode Forward Voltage	$V_{SD}$	—	0.8	1.2	V	$V_{GS} = 0\text{V}, I_S = 115\text{mA}$
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	$C_{iss}$	—	22.0	—	pF	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Output Capacitance	$C_{oss}$	—	3.2	—		
Reverse Transfer Capacitance	$C_{rss}$	—	2.0	—		
Gate Resistance	$R_G$	—	79.9	—	$\Omega$	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Total Gate Charge $V_{GS} = 10\text{V}$	$Q_g$	—	0.87	—	nC	$V_{GS} = 10\text{V}, V_{DS} = 30\text{V}, I_D = 150\text{mA}$
Total Gate Charge $V_{GS} = 4.5\text{V}$	$Q_g$	—	0.43	—		
Gate-Source Charge	$Q_{gs}$	—	0.11	—		
Gate-Drain Charge	$Q_{gd}$	—	0.11	—		
Turn-On Delay Time	$t_{D(on)}$	—	3.3	—	nS	$V_{DD} = 30\text{V}, I_D = 0.115\text{A}, V_{GEN} = 10\text{V}, R_{GEN} = 25\Omega$
Turn-On Rise Time	$t_r$	—	3.2	—		
Turn-Off Delay Time	$t_{D(off)}$	—	12.0	—		
Turn-Off Fall Time	$t_f$	—	6.3	—		

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper pad layout
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to production testing.

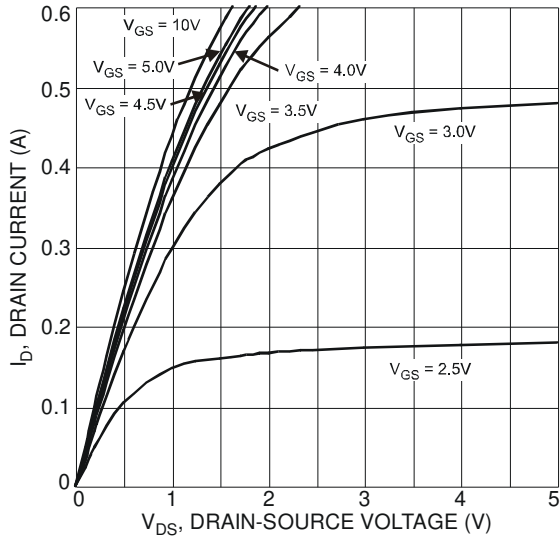


Fig.1 Typical Output Characteristic

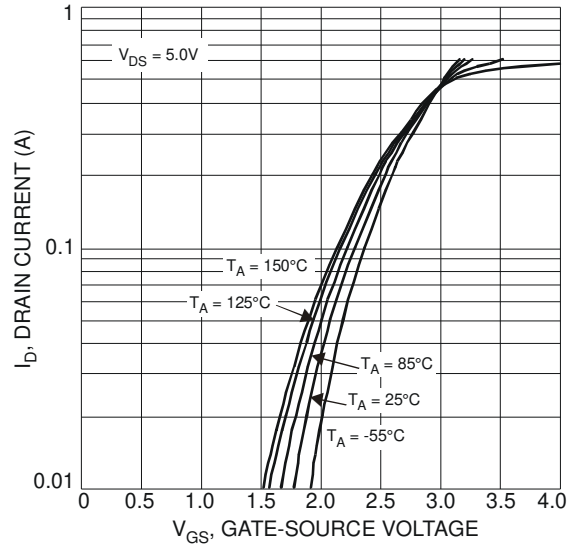


Fig.2 Typical Transfer Characteristics

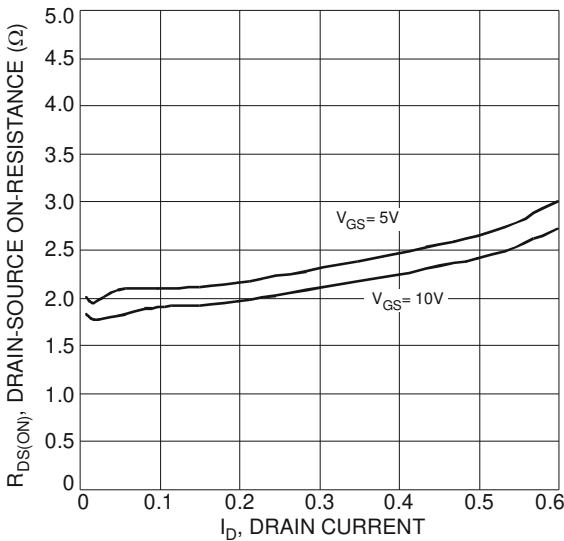


Fig. 3 Typical On-Resistance vs. Drain Current and Temperature

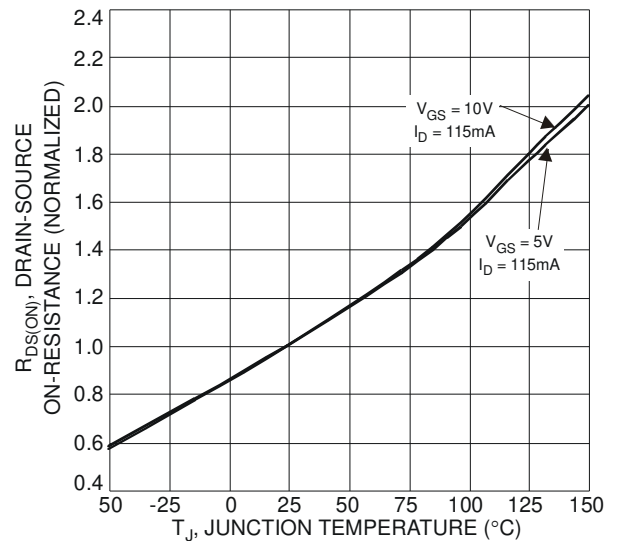


Fig. 4 On-Resistance Variation with Temperature

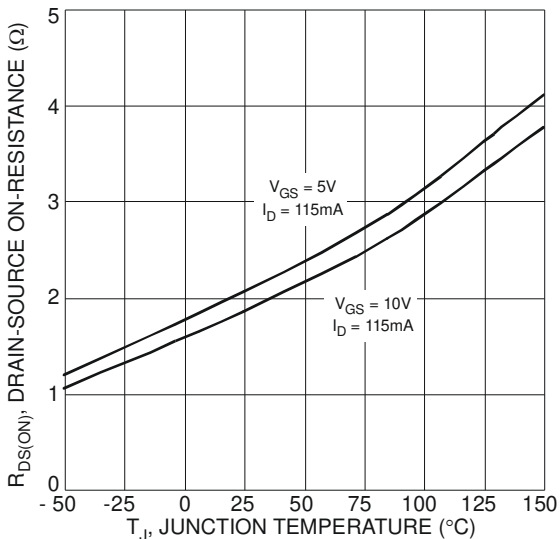


Fig. 5 On-Resistance Variation with Temperature

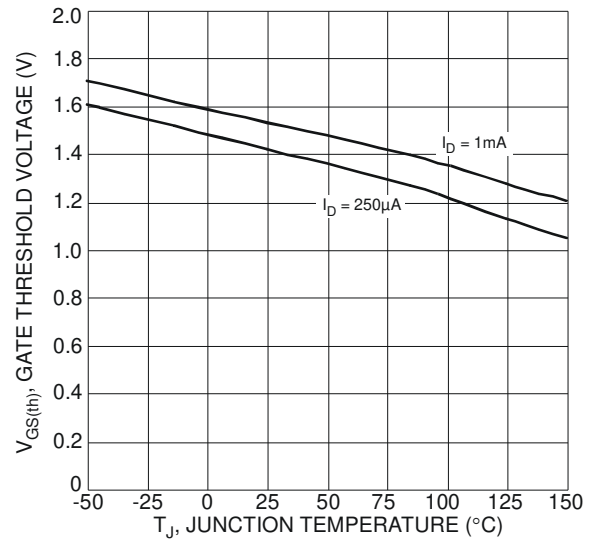


Fig. 6 Gate Threshold Variation vs. Ambient Temperature

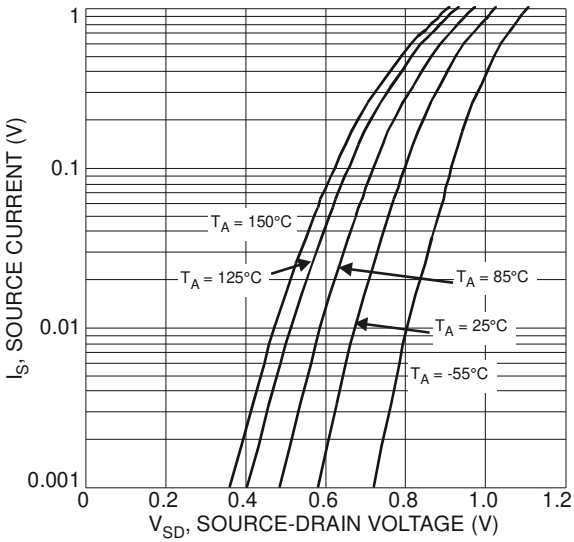


Fig. 7 Diode Forward Voltage vs. Current

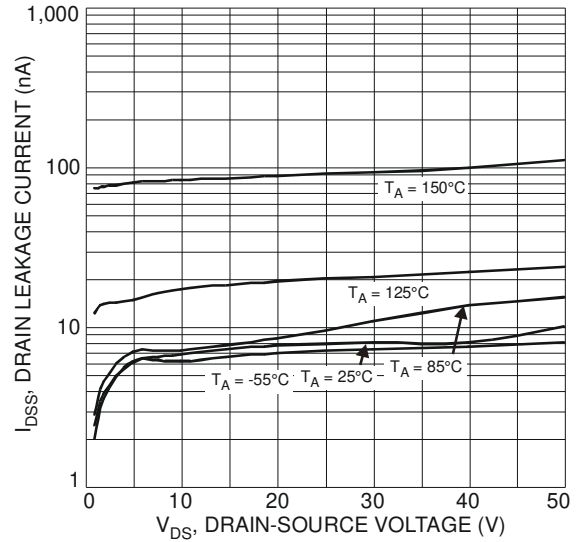


Fig. 8 Typical Drain-Source Leakage Current vs. Voltage

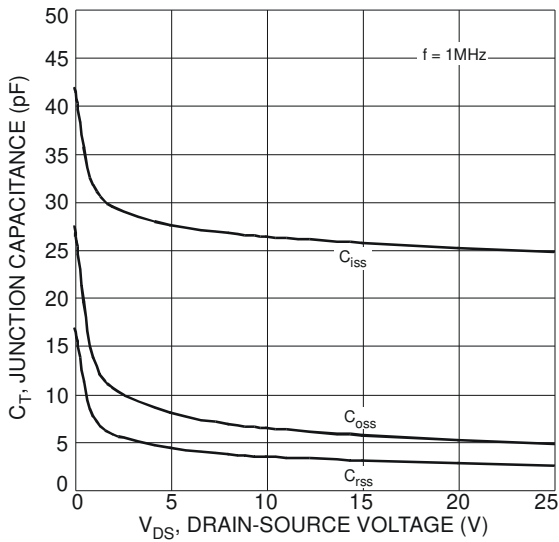


Fig. 9 Typical Junction Capacitance

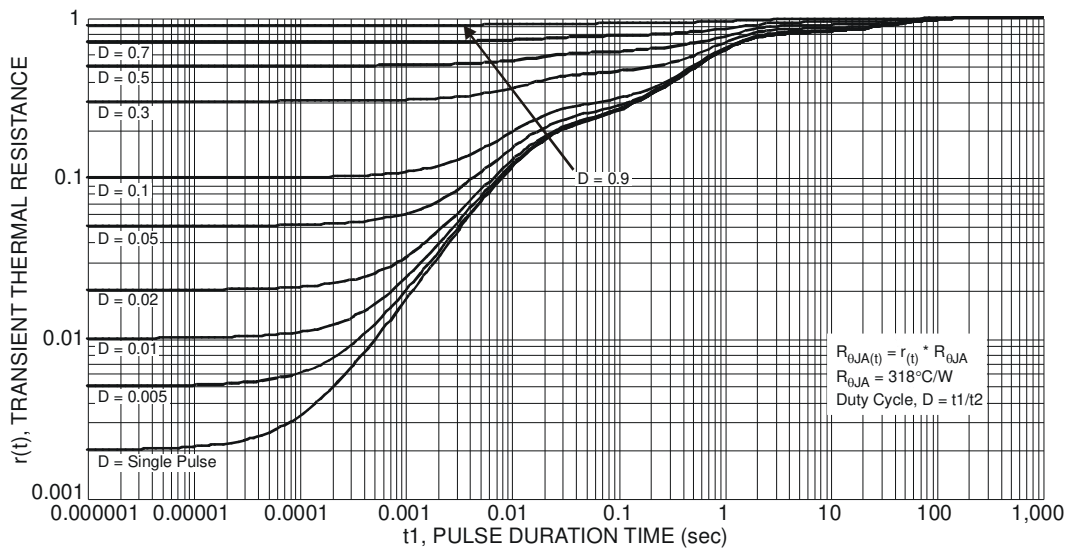


Fig. 10 Transient Thermal Resistance

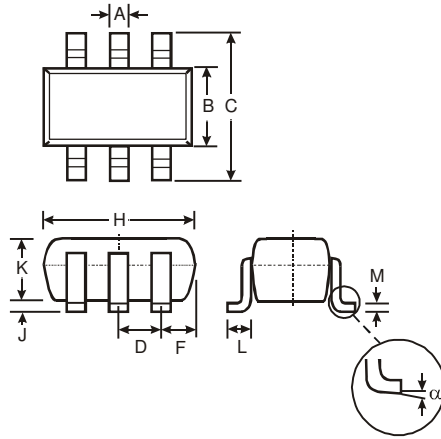
$$R_{\theta JA(t)} = r(t) * R_{\theta JA}$$

$$R_{\theta JA} = 318^{\circ}\text{C/W}$$

$$\text{Duty Cycle, } D = t1/t2$$

**Package Outline Dimensions**

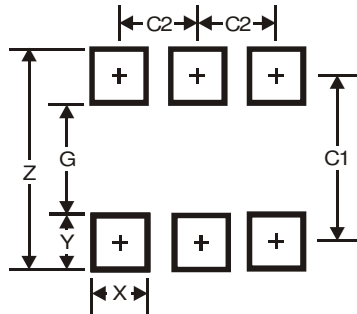
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



SOT363			
Dim	Min	Max	Typ
A	0.10	0.30	0.25
B	1.15	1.35	1.30
C	2.00	2.20	2.10
D	0.65 Typ		
F	0.40	0.45	0.425
H	1.80	2.20	2.15
J	0	0.10	0.05
K	0.90	1.00	1.00
L	0.25	0.40	0.30
M	0.10	0.22	0.11
α	0°	8°	-
<b>All Dimensions in mm</b>			

**Suggested Pad Layout**

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	2.5
G	1.3
X	0.42
Y	0.6
C1	1.9
C2	0.65

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